

S/N Unknown

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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| Applicant: | Leonard Forbes | Examiner: | Unknown |
| Serial No.: | Unknown | Group Art Unit: | Unknown |
| Filed: | Herewith | Docket: | 1303.058US2 |
| Title: | FERROELECTRIC WRITE ONCE READ ONLY MEMORY FOR ARCHIVAL STORAGE | | |

INFORMATION DISCLOSURE STATEMENT

MS Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicant respectfully requests that this Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicant requests that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicant with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Information Disclosure Statement.

Pursuant to 37 C.F.R. §1.98(d), copies of the listed documents are not provided as these references were previously cited by or submitted to the U.S. Patent Office in connection with Applicant's prior U.S. application, Serial No. 10/177082, filed on June 21, 2002, which is relied upon for an earlier filing date under 35 U.S.C. §120.

The Examiner is invited to contact the Applicant's Representative at the below-listed telephone number if there are any questions regarding this communication.

Respectfully submitted,

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By his Representatives,

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Date of Deposit: February 27, 2004

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| Application Number | Unknown |
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| First Named Inventor | Forbes, Leonard |
| Group Art Unit | Unknown |
| Examiner Name | Unknown |

Sheet 1 of 8

Attorney Docket No: 1303.058US2

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| Examiner Name | Unknown |

Sheet 2 of 8

Attorney Docket No: 1303.058US2

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| Examiner Name | Unknown |

Sheet 3 of 8

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| Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i> | <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td colspan="2" style="text-align: left;"><i>Complete if Known</i></td> </tr> <tr> <td style="width: 50%;">Application Number</td> <td>Unknown</td> </tr> <tr> <td>Filing Date</td> <td>Even Date Herewith</td> </tr> <tr> <td>First Named Inventor</td> <td>Forbes, Leonard</td> </tr> <tr> <td>Group Art Unit</td> <td>Unknown</td> </tr> <tr> <td>Examiner Name</td> <td>Unknown</td> </tr> </table> | <i>Complete if Known</i> | | Application Number | Unknown | Filing Date | Even Date Herewith | First Named Inventor | Forbes, Leonard | Group Art Unit | Unknown | Examiner Name | Unknown |
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| Group Art Unit | Unknown | | | | | | | | | | | | |
| Examiner Name | Unknown | | | | | | | | | | | | |
| Sheet 4 of 8 | Attorney Docket No: 1303.058US2 | | | | | | | | | | | | |

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Sheet 6 of 8

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| | Filing Date | Even Date Herewith |
| | First Named Inventor | Forbes, Leonard |
| | Group Art Unit | Unknown |
| | Examiner Name | Unknown |
| Sheet 7 of 8 | Attorney Docket No: 1303.058US2 | |

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| | Group Art Unit | Unknown |
| | Examiner Name | Unknown |
| Sheet 8 of 8 | Attorney Docket No: 1303.058US2 | |

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